Quad 2-Input OR Gate

MC74VHC32

The MC74VHC32 is an advanced high speed CMOS 2-input OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

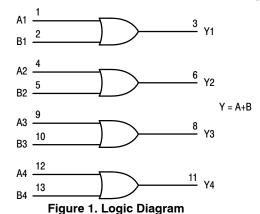
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 3.8 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2.0 \,\mu\text{A}$ (Max) at $T_{A} = 25^{\circ}\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 48 FETs or 12 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



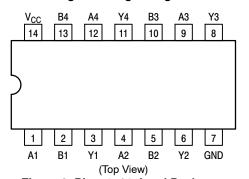


Figure 2. Pinout: 14-Lead Packages

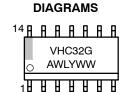


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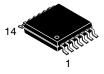
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SOIC-14 **D SUFFIX CASE 751A**



MARKING



TSSOP DT SUFFIX CASE 948G



= Assembly Location

= Wafer Lot WL, L = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

| Inputs | | Output |
|--------|---|--------|
| Α | В | Υ |
| L | L | L |
| L | Н | Н |
| Н | L | Н |
| Н | Н | Н |

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MC74VHC32

MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit |
|------------------|---|---|-------------|------|
| V _{CC} | DC Supply Voltage | DC Supply Voltage | | |
| V _{in} | DC Input Voltage | -0.5 to +7.0 | V | |
| V _{out} | DC Output Voltage | -0.5 to V _{CC} +0.5 | V | |
| I _{IK} | Input Diode Current | -20 | mA | |
| lok | Output Diode Current | ±20 | mA | |
| I _{out} | DC Output Current, per Pin | | ±25 | mA |
| I _{CC} | DC Supply Current, V _{CC} and GN | ID Pins | ±50 | mA |
| P _D | Power Dissipation in Still Air, | SOIC Package [†] TSSOP Package [†] | 500 450 | mW |
| T _{stg} | Storage Temperature | | -65 to +150 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating – SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|---------------------------------|--|--------|-----------------|------|
| V _{CC} | DC Supply Voltage | 2.0 | 5.5 | V |
| V _{in} | DC Input Voltage | 0 | 5.5 | V |
| V _{out} | DC Output Voltage | 0 | V _{CC} | V |
| T _A | Operating Temperature | -40 | +125 | °C |
| t _r , t _f | Input Rise and Fall Time $ V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V} $ $ V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V} $ | 0 0 | 100 20 | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

| | | | V _{CC} | T, | _A = 25° | С | T _A = -40°0 | C to 125°C | |
|-----------------|--------------------------------------|--|-------------------|-------------------------------|--------------------|-------------------------------|-------------------------------|-------------------------------|------|
| Symbol | Parameter | Test Conditions | v | Min | Тур | Max | Min | Max | Unit |
| V _{IH} | Minimum High-Level Input Voltage | | 2.0 3.0 to 5.5 | 1.50 V _{CC} x 0.7 | | | 1.50 V _{CC} x 0.7 | | V |
| V _{IL} | Maximum Low-Level Input Voltage | | 2.0 3.0 to 5.5 | | | 0.50 V _{CC} x 0.3 | | 0.50 V _{CC} x 0.3 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$ | 2.0 3.0 4.5 | 1.9 2.9 4.4 | 2.0 3.0 4.5 | | 1.9 2.9 4.4 | | V |
| | | $V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4.0 \text{ mA}$ $I_{OH} = -8.0 \text{ mA}$ | 3.0 4.5 | 2.58 3.94 | | | 2.48 3.80 | | |
| V _{OL} | Maximum Low-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$ | 2.0 3.0 4.5 | | 0.0 0.0 0.0 | 0.1 0.1 0.1 | | 0.1 0.1 0.1 | V |
| | | $V_{in} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 4.0 \text{ mA} \\ I_{OL} = 8.0 \text{ mA}$ | 3.0 4.5 | | | 0.36 0.36 | | 0.44 0.44 | |
| l _{in} | Maximum Input Leakage Current | V _{in} = 5.5 V or GND | 0 to 5.5 | | | ±0.1 | | ±1.0 | μΑ |
| I _{CC} | Maximum Quiescent Supply Current | V _{in} = V _{CC} or GND | 5.5 | | | 2.0 | | 20.0 | μΑ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

| | | | T _A = 25°C | | T _A = -40°C to 125°C | | | |
|--|----------------------------|--|-----------------------|------------|---------------------------------|------------|-------------|------|
| Symbol | Parameter | Test Conditions | Min | Тур | Max | Min | Max | Unit |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, | $V_{CC} = 3.3 \pm 0.3 \ VC_L = 15 \ pF$ $C_L = 50 \ pF$ | | 5.5 8.0 | 7.9 11.4 | 1.0 1.0 | 9.5 13.0 | ns |
| | A or B to Y | $V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$ | | 3.8 5.3 | 5.5 7.5 | 1.0 1.0 | 6.5 8.5 | |
| C _{in} | Maximum Input Capacitance | | | 4 | 10 | | 10 | pF |

| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|----------|--|---|----|
| C_{PD} | Power Dissipation Capacitance (Note 1) | 14 | pF |

C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$, $C_L = 50 \text{ pF}$, $V_{CC} = 5.0 \text{ V}$)

| | T _A = 25°C | | 25°C | |
|------------------|--|------|------|------|
| Symbol | Characteristic | Тур | Max | Unit |
| V _{OLP} | Quiet Output Maximum Dynamic V _{OL} | 0.3 | 0.8 | V |
| V _{OLV} | Quiet Output Minimum Dynamic V _{OL} | -0.3 | -0.8 | V |
| V _{IHD} | Minimum High Level Dynamic Input Voltage | | 3.5 | V |
| V _{ILD} | Maximum Low Level Dynamic Input Voltage | | 1.5 | V |

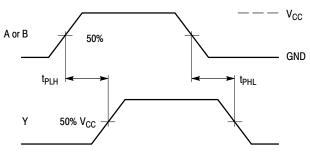
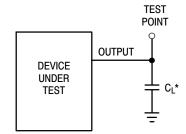


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

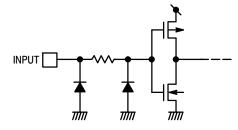


Figure 5. Input Equivalent Circuit

MC74VHC32

ORDERING INFORMATION

| Device | Package | Shipping [†] | |
|------------------|-----------------------|---------------------------|--|
| MC74VHC32DR2G | SOIC-14 | 2500 Unito / Tana & Book | |
| NLV74VHC32DR2G* | (Pb-Free) | 2500 Units / Tape & Reel | |
| MC74VHC32DTG | | 96 Units / Rail | |
| MC74VHC32DTR2G | TSSOP-14 (Pb-Free) | 2500 Units / Tape & Reel | |
| NLV74VHC32DTR2G* | | 2500 Offits / Tape & neer | |

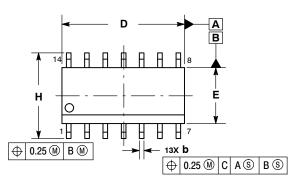
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.



△ 0.10

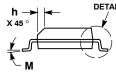
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





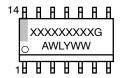




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

| | MILLIN | IETERS | INCHES | | |
|-----|----------|--------|--------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 1.35 | 1.75 | 0.054 | 0.068 | |
| A1 | 0.10 | 0.25 | 0.004 | 0.010 | |
| АЗ | 0.19 | 0.25 | 0.008 | 0.010 | |
| b | 0.35 | 0.49 | 0.014 | 0.019 | |
| D | 8.55 | 8.75 | 0.337 | 0.344 | |
| Е | 3.80 | 4.00 | 0.150 | 0.157 | |
| е | 1.27 BSC | | 0.050 | BSC | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 | |
| h | 0.25 | 0.50 | 0.010 | 0.019 | |
| Ĺ | 0.40 | 1.25 | 0.016 | 0.049 | |
| М | 0 ° | 7° | 0 ° | 7° | |

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

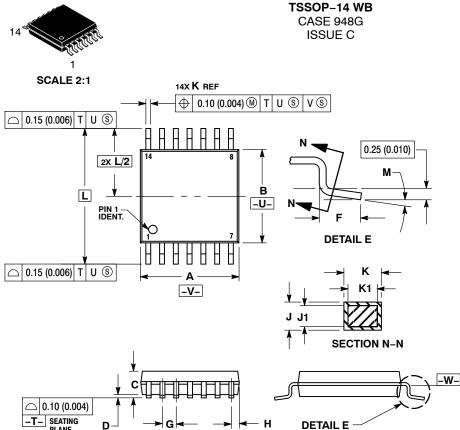
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

| STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 2: CANCELLED | STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE | STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE |
|---|---|---|---|
| STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE | STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE | STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE | STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE |

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DATE 17 FEB 2016

- NOTES.

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 2. CONTROLLING DIMENSION: MILLIMETER.

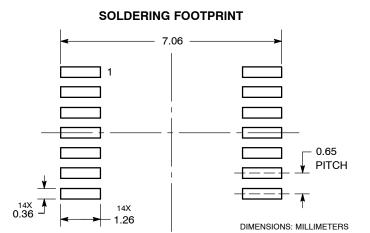
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

| | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.90 | 5.10 | 0.193 | 0.200 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | - | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC | | 0.026 BSC | |
| Н | 0.50 | 0.60 | 0.020 | 0.024 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 BSC | | 0.252 BSC | |
| М | 0° | 8° | 0° | 8 ° |

GENERIC MARKING DIAGRAM*





= Assembly Location

= Wafer Lot = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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